
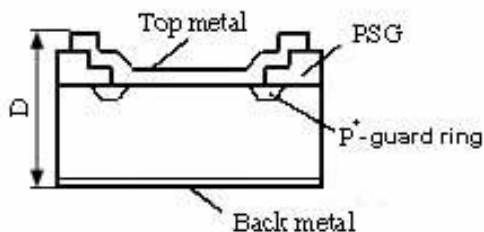
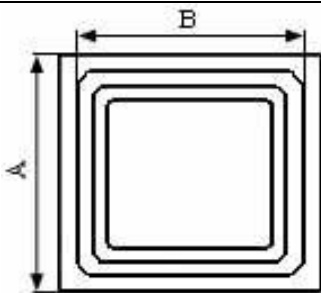


		10A/60V. Die Size-115mil.		
				
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_{BR}	V	60	65
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25°C , $I_F=10,0\text{A}$;	V_F	V	0,55	0,53
Maximum Reverse Current @ 25°C , $V_R=65\text{V}$ @ 25°C , $V_R=60\text{V}$ @ 125°C , $V_R=60\text{V}$	I_R	mA	- 0,150 70,0	0,150 0,100 60,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	200	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$, $f=1\text{kHz}$., $T_J<150^\circ\text{C}$.	I_{RRM}	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	$\text{V}/\mu\text{s}$	10.000	
Operating Junction Temperature	T_J	$^\circ\text{C}$	150	



DIM	ITEM	μm
A_x A_y	Wafer Form Die Size	2920 2920
B_x B_y	Top Metal Size	2780 2780
D	Thickness	300max.
	Scribe line Width	80

Top metal:

- a) **Al** – for Wire Bonding;
 - b) **Al-Ni-Ag** – for Soldering.
- Backside metal: **Ti-Ni-Ag**.